

NOT RECOMMENDED FOR NEW DESIGN **USE DMN61D9UDW**



DMN5L06DWK

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- **Dual N-Channel MOSFET**
- Low On-Resistance (1.0V Max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

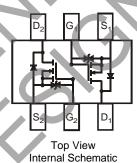
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.006 grams (Approximate)





SOT363



Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN5L06DWK-7	SOT363	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



DAB = Marking Code YM = Date Code Marking Y = Year ex: G = 2019 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008		2012	2013	2014	2015	2016	2017	2018	2019
Code	T	U	V		Z	Α	В	С	D	Е	F	G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



NOT RECOMMENDED FOR NEW DESIGN **USE DMN61D9UDW**

DMN5L06DWK

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current Continuous		305	m ^
Pulsed (Note 6)	ID	800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	250	mW
Thermal Resistance, Junction to Ambient	R _{0JA}	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

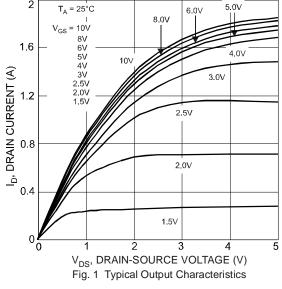
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

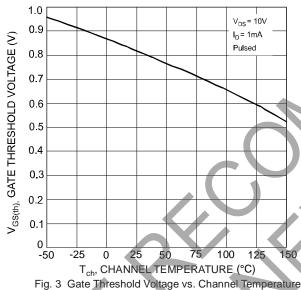
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	50	· —		V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current @ T _C = +25°C	1 _{DSS}	7		60	nΑ	$V_{DS} = 50V$, $V_{GS} = 0V$	
				<u> </u>	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
Gate-Body Leakage	Igss	_	*	500	nΑ	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
				50	nA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	0.49	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		_		3.0		$V_{GS} = 1.8V, I_D = 50mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_		2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$	
			_	2.0		$V_{GS} = 5.0V, I_D = 50mA$	
On-State Drain Current	ID(ON)	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$	
Forward Transconductance	Y _{FS}	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
Source-Drain Diode Forward Voltage	V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	_	50	рF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Output Capacitance	Coss	_	_	25	рF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	_	5.0	pF	1 = 1.001112	
Gate Resistance	R_{G}	_	65	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q _G	_	0.4	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Source Charge	Q _{GS}	_	0.1	_	nC		
Gate-Drain Charge	Q_{GD}	_	0.1	_	nC	$I_D = 0.25A$	
Turn-On Delay Time	t _{D(ON)}	_	2.1	_	ns		
Turn-On Rise Time	t _R	_	1.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	14.4	_	ns	$R_G = 25\Omega$, $I_D = 0.2A$	
Turn-Off Fall Time	t _F		8.4	_	ns		

Notes:

- Device mounted on FR-4 PCB.
 Hulse width ≤10μS, Duty Cycle ≤1%.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







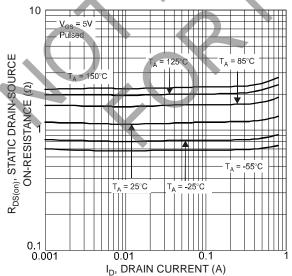
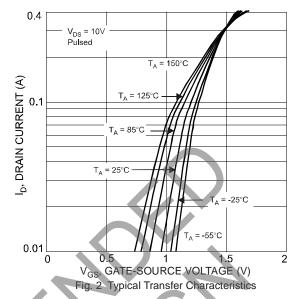


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



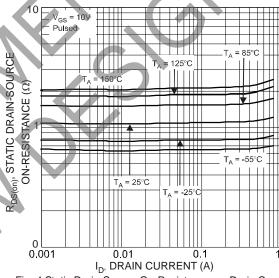


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

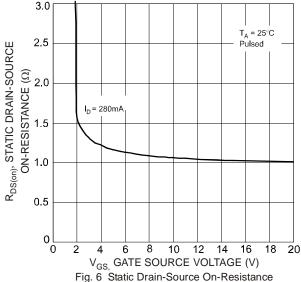


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



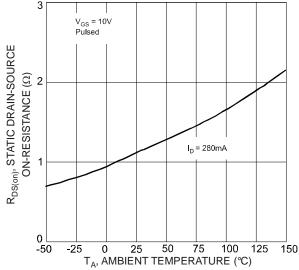


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

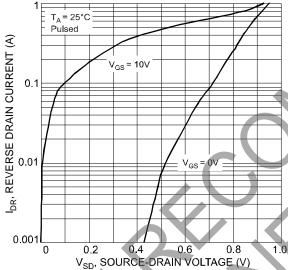
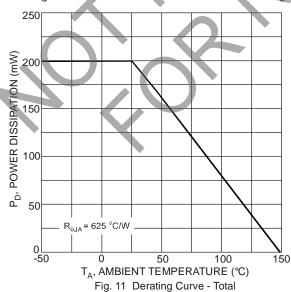


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



0.1

V_{GS} = 0V
Pulsed

T_A = 150°C

T_A = 25°C

T_A = 25°C

T_A = -25°C

V_{SD}, SOURCE-DRAIN VOLTAGE (V)

Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

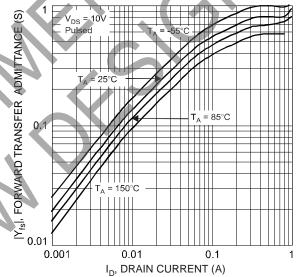


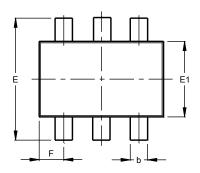
Fig.10 Forward Transfer Admittance vs. Drain Current

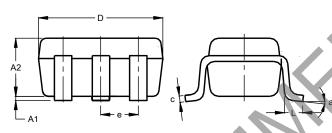


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



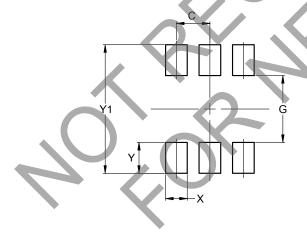


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
E	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	0.650 BSC					
F	0.40	0.45	0.425			
1	0.25	0.40	0.30			
а	ô	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value		
Dillielisions	(in mm)		
С	0.650		
G	1.300		
Х	0.420		
Υ	0.600		
V1	2.500		



NOT RECOMMENDED FOR NEW DESIGN USE <u>DMN61D9UDW</u>

DMN5L06DWK

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com